AMENDMENTS TO THE CLAIMS

Claims 1-5 (canceled).

6. (original) A method for forming a memory device, comprising:

forming a gate dielectric on a semiconductor substrate;

forming source and drain regions on opposite sides of said gate dielectric;

forming a floating gate on said gate dielectric;

forming a silicon-doped Al_2O_3 layer by chemical vapor deposition on said floating gate; and

forming a control gate on said doped Al_2O_3 layer.

7. (original) The method of claim 6, wherein said step of forming said silicon-doped Al_2O_3 layer is performed at an energy of approximately 10keV and at a dose of approximately $1x10^{14}$ /cm^2 to $1x10^{15}$/cm^2.

8. (original) The method of claim 6 further comprising forming a silicide layer on top of said control gate.

9. (original) The method of claim 6, wherein said gate dielectric is formed of a material selected from the group consisting of oxynitride and oxide.

10. (original) The method of claim 6, wherein said memory device is a flash memory device.

Claims 11-26 (canceled).